

HIGH NOISE REDUCTION HIGH-SPEED ANALOG OUTPUT TYPE
5-PIN SOP PHOTOCOUPLER

DESCRIPTION

The PS8701 is an optically coupled isolator containing a GaAlAs LED on the light emitting diode (input side) and a PIN photodiode and a high-speed amplifier transistor on the output side on one chip.

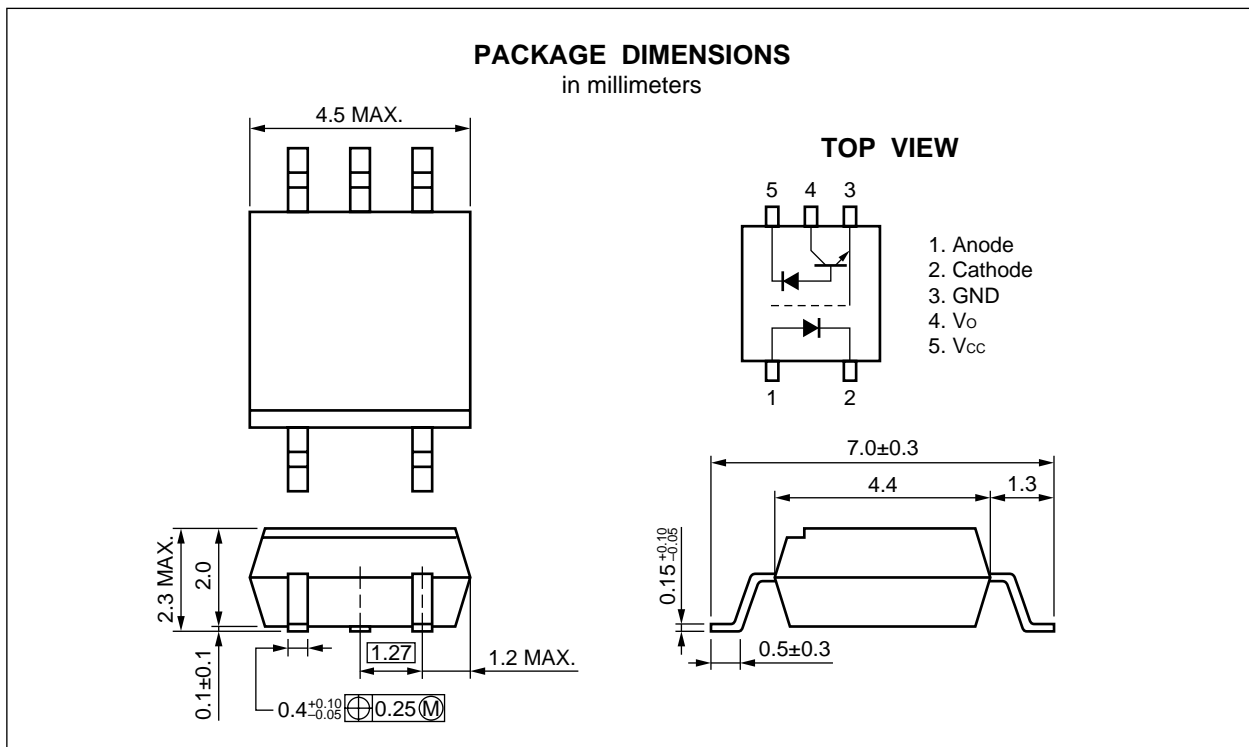
This is a plastic SOP (Small Out-line Package) type for high density applications.

FEATURES

- High common mode transient immunity ($C_{MH}, C_{ML} = \pm 10 \text{ kV}/\mu\text{s}$ MIN.)
- High supply voltage ($V_{CC} = 35 \text{ V}$)
- High isolation voltage ($BV = 2\,500 \text{ Vr.m.s.}$)
- High-speed response ($t_{PHL} = 0.8 \mu\text{s}$ MAX., $t_{PLH} = 1.2 \mu\text{s}$ MAX.)
- Taping product number (PS8701-E3, E4, F3, F4)

APPLICATIONS

- Computer and peripheral manufactures
- General purpose inverter
- Substitutions for relays and pulse transformers
- Power supply



The information in this document is subject to change without notice.

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

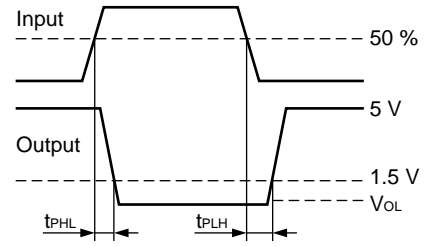
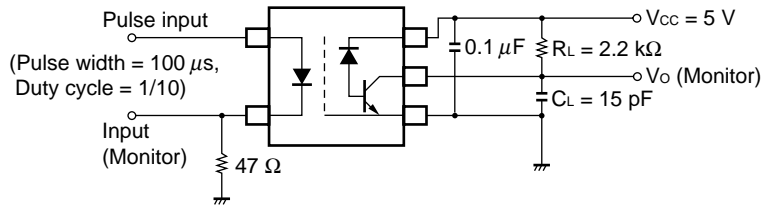
| Parameter | | Symbol | Ratings | Unit |
|---------------------------------|-------------------|------------------|-------------|---------|
| Diode | Forward Current | I _F | 25 | mA |
| | Reverse Voltage | V _R | 3.0 | V |
| | Power Dissipation | P _D | 45 | mW |
| Detector | Supply Voltage | V _{CC} | 35 | V |
| | Output Voltage | V _O | 35 | V |
| | Output Current | I _O | 8.0 | mA |
| | Power Dissipation | P _C | 100 | mW |
| Isolation Voltage ^{*1} | | BV | 2 500 | Vr.m.s. |
| Operating Ambient Temperature | | T _A | -55 to +100 | °C |
| Storage Temperature | | T _{stg} | -55 to +125 | °C |

*1 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

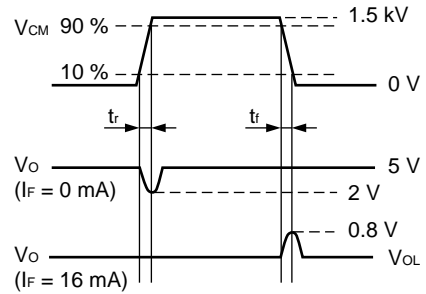
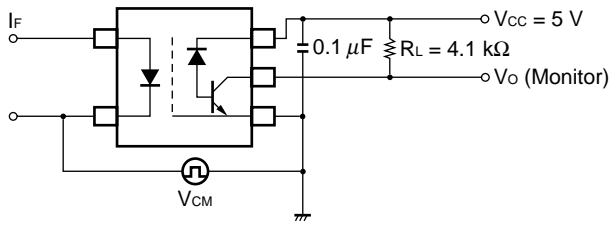
| Parameter | | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-----------|---|---------------------|--|------------------|------|------|-------|
| Diode | Forward Voltage | V _F | I _F = 16 mA | | 1.7 | 2.2 | V |
| | Reverse Current | I _R | V _R = 3 V | | | 10 | μA |
| | Forward Voltage Temperature Coefficient | ΔV _F /ΔT | I _F = 16 mA | | -1.6 | | mV/°C |
| | Terminal Capacitance | C _t | V = 0 V, f = 1 MHz | | 60 | | pF |
| Detector | High Level Output Current | I _{OH} (1) | I _F = 0 mA, V _{CC} = V _O = 5.5 V | | 3 | 500 | nA |
| | High Level Output Current | I _{OH} (2) | I _F = 0 mA, V _{CC} = V _O = 30 V | | | 100 | μA |
| | Low Level Output Voltage | V _{OL} | I _F = 16 mA, V _{CC} = 4.5 V, I _O = 1.2 mA | | 0.1 | 0.4 | V |
| | Low Level Supply Current | I _{CC} L | I _F = 16 mA, V _O = open, V _{CC} = 30 V | | 50 | | μA |
| | High Level Supply Current | I _{CC} H | I _F = 0 mA, V _O = open, V _{CC} = 30 V | | 0.01 | 2 | |
| Coupled | Current Transfer Ratio | CTR | I _F = 16 mA, V _{CC} = 4.5 V, V _O = 0.4 V | 15 | 20 | 35 | % |
| | Isolation Resistance | R _{I-O} | V _{I-O} = 1 kV _{DC} , RH = 40 to 60 % | 10 ¹¹ | | | Ω |
| | Isolation Capacitance | C _{I-O} | V = 0 V, f = 1 MHz | | 0.4 | | pF |
| | Propagation Delay Time (H → L) ^{*1} | t _{PHL} | I _F = 16 mA, V _{CC} = 5 V, R _L = 2.2 kΩ, C _L = 15 pF | | 0.5 | 0.8 | μs |
| | Propagation Delay Time (L → H) ^{*1} | t _{PLH} | | | 0.6 | 1.2 | |
| | Common Mode Transient Immunity at High Level Output ^{*2} | C _{MH} | I _F = 0 mA, V _{CC} = 5 V, R _L = 4.1 kΩ, V _{CM} = 1.5 kV | 10 | | | kV/μs |
| | Common Mode Transient Immunity at Low Level Output ^{*2} | C _{ML} | I _F = 16 mA, V _{CC} = 5 V, R _L = 4.1 kΩ, V _{CM} = 1.5 kV | -10 | | | |

***1 Test circuit for propagation delay time**



C_L is approximately 15 pF which includes probe and stray wiring capacitance

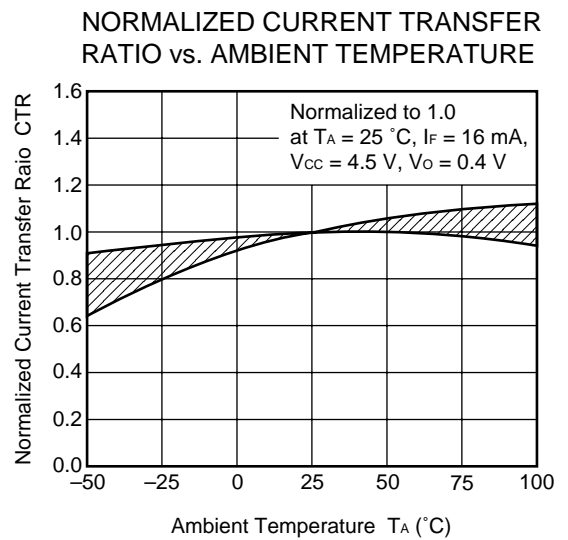
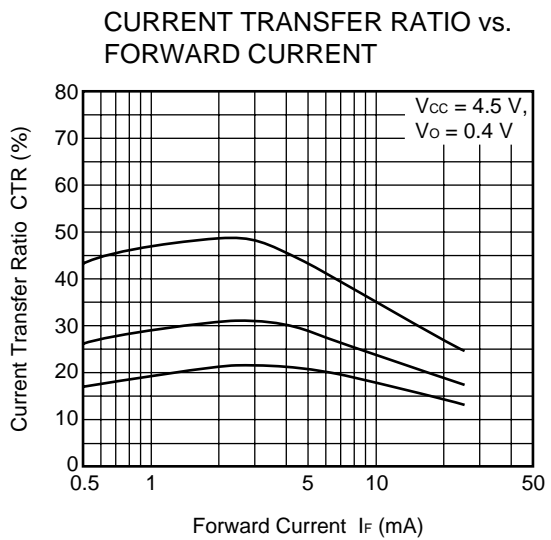
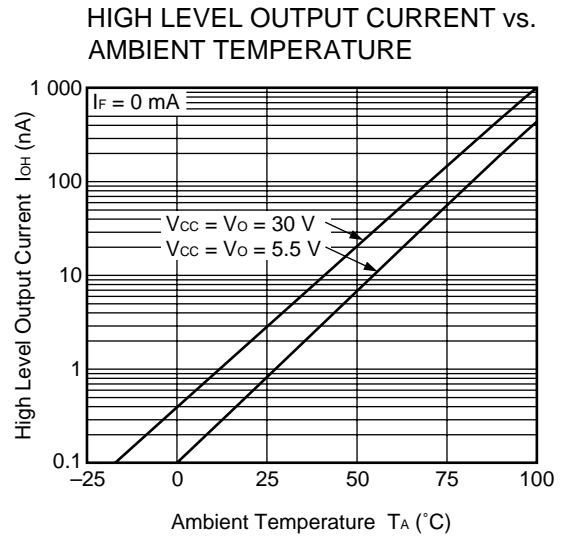
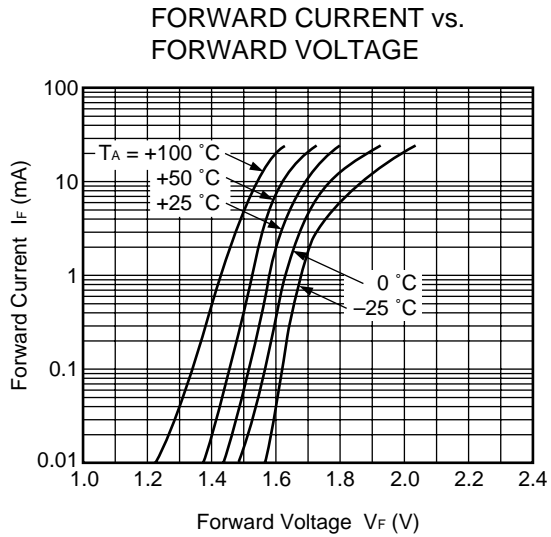
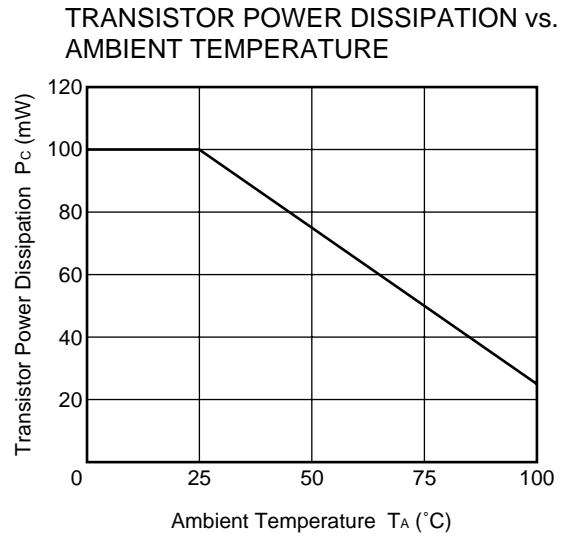
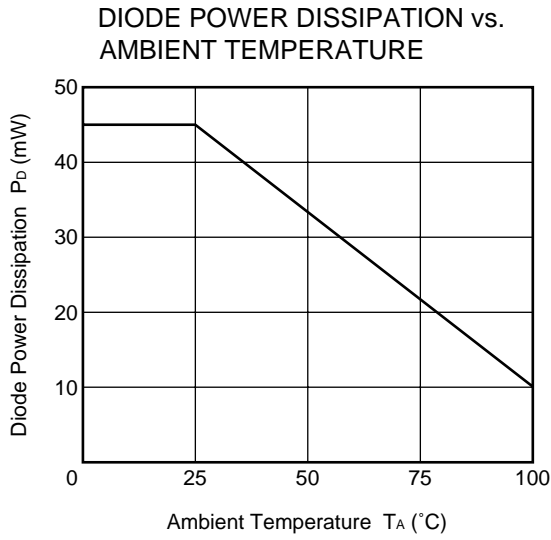
***2 Test circuit for common mode transient immunity**



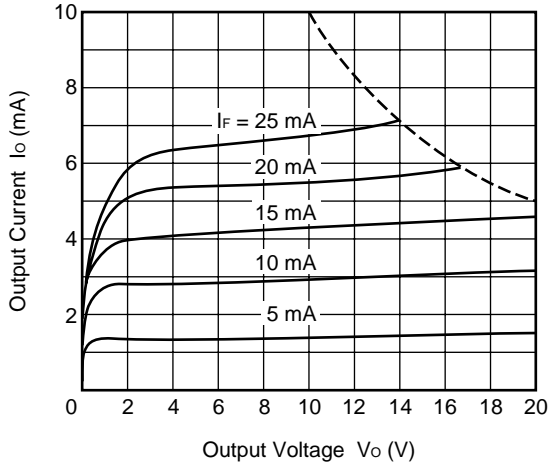
USAGE CAUTIONS

1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
2. By-pase capacitor of more than 0.1 μF is used between V_{CC} and GND near device.

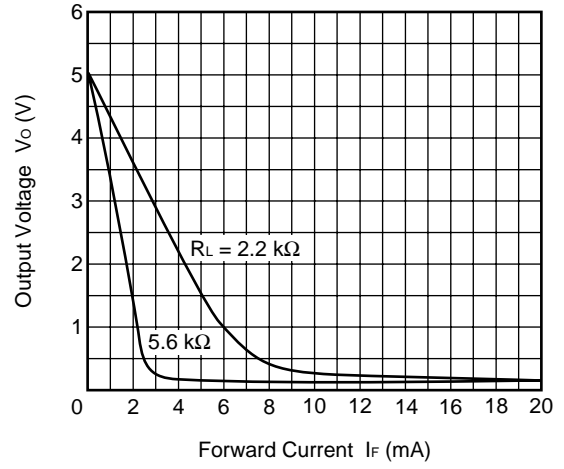
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified)



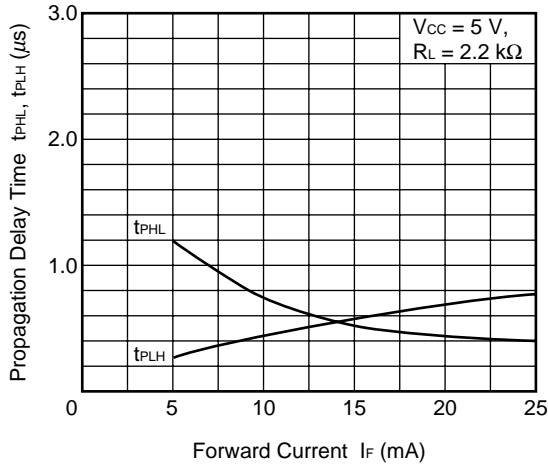
OUTPUT CURRENT vs. OUTPUT VOLTAGE



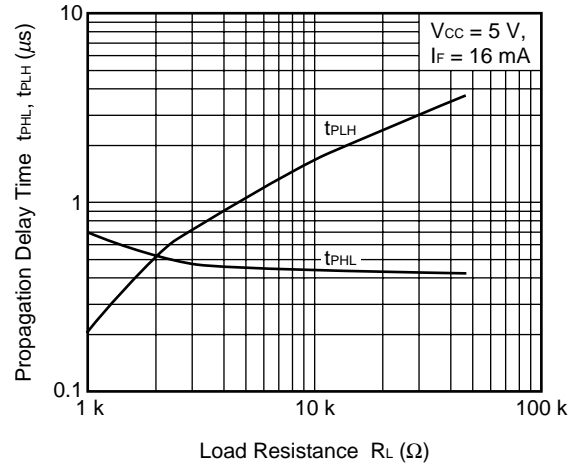
OUTPUT VOLTAGE vs. FORWARD CURRENT



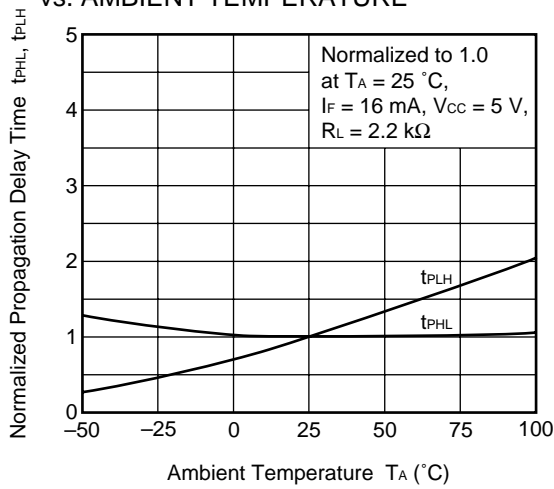
PROPAGATION DELAY TIME vs. FORWARD CURRENT



PROPAGATION DELAY TIME vs. LOAD RESISTANCE

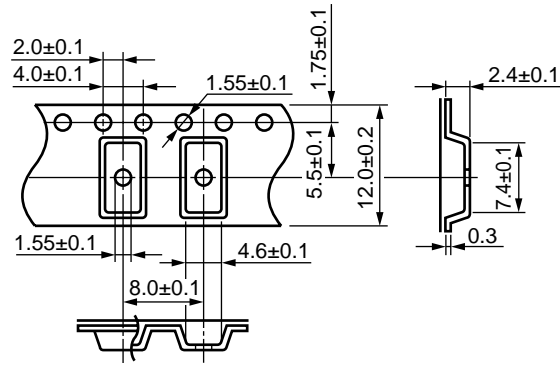


NORMALIZED PROPAGATION DELAY TIME vs. AMBIENT TEMPERATURE

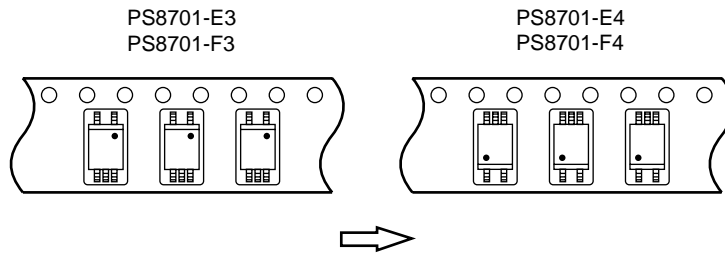


TAPING SPECIFICATIONS (in millimeters)

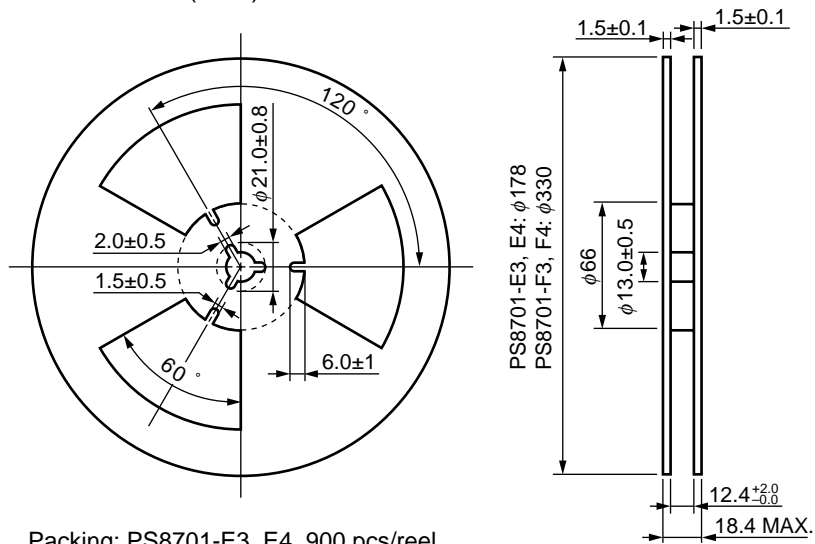
Outline and Dimensions (Tape)



Taping Direction



Outline and Dimensions (Reel)



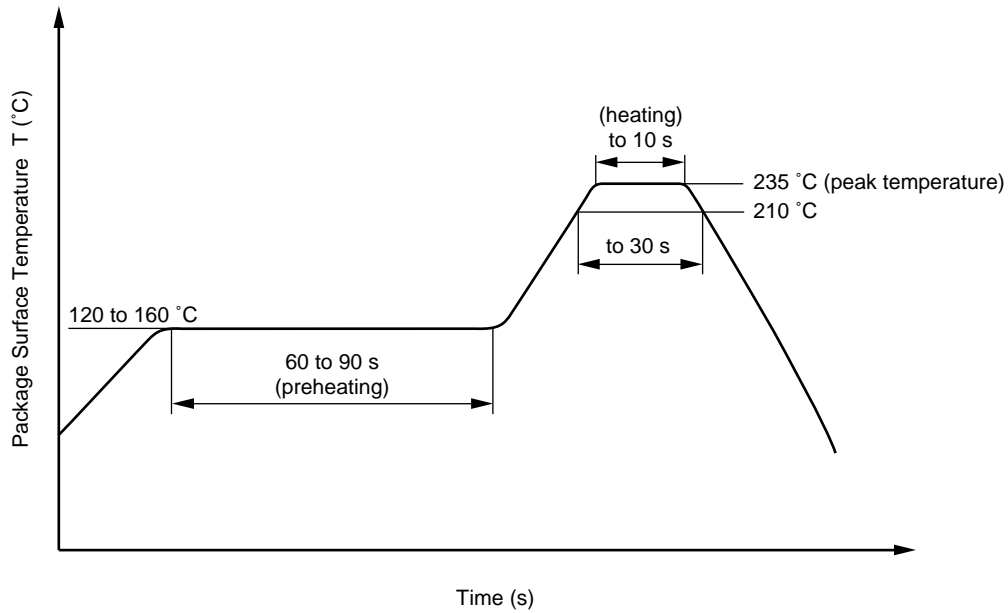
Packing: PS8701-E3, E4 900 pcs/reel
 PS8701-F3, F4 3 500 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

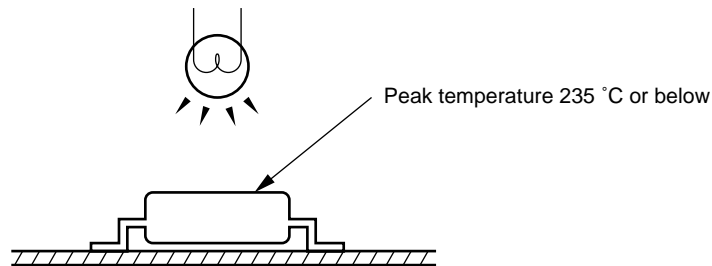
(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



Caution Please avoid to removed the residual flux by water after the first reflow processes.



(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Anti-radioactive design is not implemented in this product.